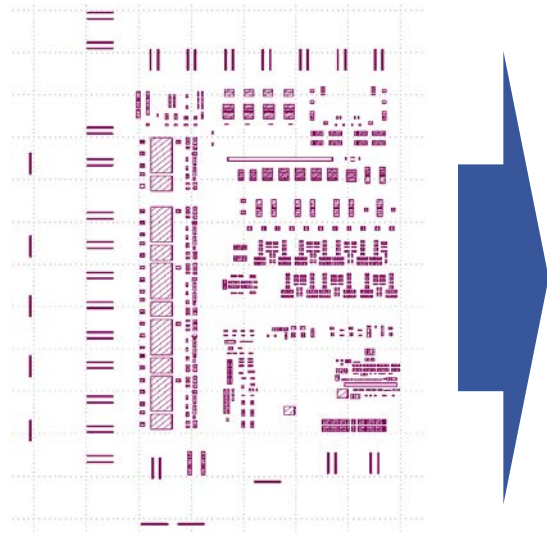


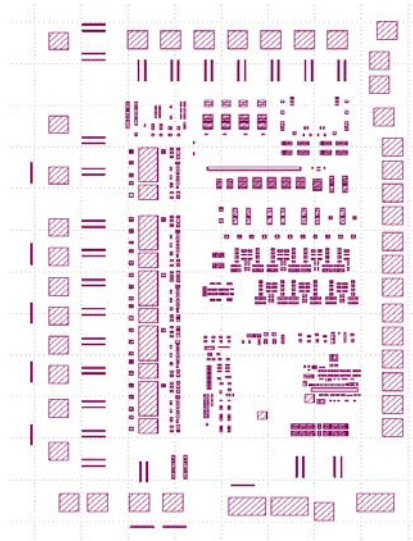
TGATE Mask Change

TGATE mask defines areas of thick gate oxide for high voltage devices on the process. A single mask change affecting only the bond pad area of the HV Die on the AD7280 is proposed. There is no process flow change involved in this change. This change will have no electrical effect on the product.

'Before'



'After'



Reference Bond Pad Layout

